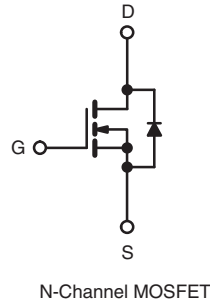
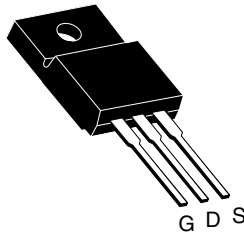


## Power MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	400	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10$ V	1.8
$Q_g$ (Max.) (nC)	20	
$Q_{gs}$ (nC)	3.3	
$Q_{gd}$ (nC)	11	
Configuration	Single	

**TO-220 FULLPAK**


### FEATURES

- Isolated package
- High voltage isolation = 2.5 kV<sub>RMS</sub> (t = 60 s; f = 60 Hz)
- Sink to lead creepage distance = 4.8 mm
- Dynamic dV/dt rating
- Low thermal resistance
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



### Note

\* This datasheet provides information about parts that are RoHS-compliant and/or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information/tables in this datasheet for details.

### DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 FULLPAK eliminates the need for additional insulating hardware in commercial-industrial applications. The molding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The FULLPAK is mounted to a heatsink using a single clip or by a single screw fixing.

ORDERING INFORMATION	
Package	TO-220 FULLPAK
Lead (Pb)-free	IRFI720GPbF SiHFI720G-E3
SnPb	IRFI720G SiHFI720G

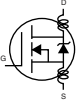
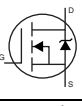
ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)					
PARAMETER	SYMBOL		LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$		400	V	
Gate-Source Voltage	$V_{GS}$		$\pm 20$		
Continuous Drain Current	$V_{GS}$ at 10 V	$T_C = 25$ °C	2.6	A	
		$T_C = 100$ °C	1.7		
Pulsed Drain Current <sup>a</sup>	$I_{DM}$		10		
Linear Derating Factor			0.24	W/°C	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$		150	mJ	
Repetitive Avalanche Current <sup>a</sup>	$I_{AR}$		2.6	A	
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$		3.0	mJ	
Maximum Power Dissipation	$T_C = 25$ °C		$P_D$	30	W
Peak Diode Recovery dV/dt <sup>c</sup>			dV/dt	4.0	V/ns
Operating Junction and Storage Temperature Range			$T_J, T_{stg}$	-55 to +150	°C
Soldering Recommendations (Peak Temperature) <sup>d</sup>	for 10 s			300	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C, L = 38 mH,  $R_G = 25$   $\Omega$ ,  $I_{AS} = 2.6$  A (see fig. 12).
- $I_{SD} \leq 3.3$  A,  $dI/dt \leq 65$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150$  °C.
- 1.6 mm from case.



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	65	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	4.1	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		400	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	0.51	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	$\mu\text{A}$
		$V_{DS} = 320\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 1.6\text{ A}^b$	-	-	1.8	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 1.6\text{ A}^b$		1.5	-	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}, \text{ see fig. 5}$		-	410	-	pF
Output Capacitance	$C_{oss}$			-	120	-	
Reverse Transfer Capacitance	$C_{rss}$			-	47	-	
Drain to Sink Capacitance	$C$	$f = 1.0\text{ MHz}$		-	12	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 3.3\text{ A}, V_{DS} = 320\text{ V}, \text{ see fig. 6 and 13}^b$	-	-	20	nC
Gate-Source Charge	$Q_{gs}$			-	-	3.3	
Gate-Drain Charge	$Q_{gd}$			-	-	11	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 200\text{ V}, I_D = 3.3\text{ A}, R_G = 18\text{ }\Omega, R_D = 56\text{ }\Omega, \text{ see fig. 10}^b$		-	10	-	ns
Rise Time	$t_r$			-	14	-	
Turn-Off Delay Time	$t_{d(off)}$			-	30	-	
Fall Time	$t_f$			-	13	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	$L_S$			-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	2.6	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	-	10	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 2.6\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.6	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 3.3\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	300	600	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	1.5	3.0	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

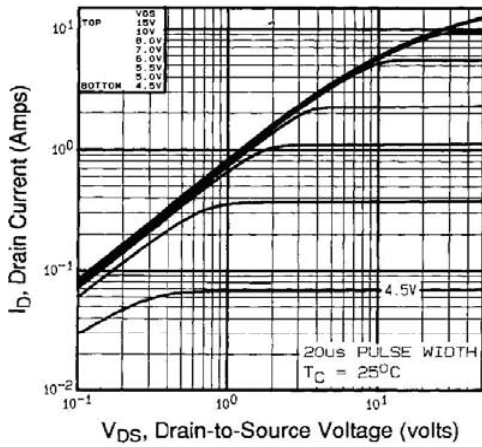


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$

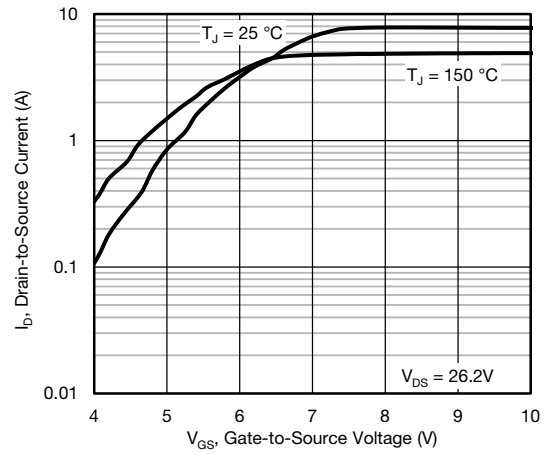


Fig. 3 - Typical Transfer Characteristics

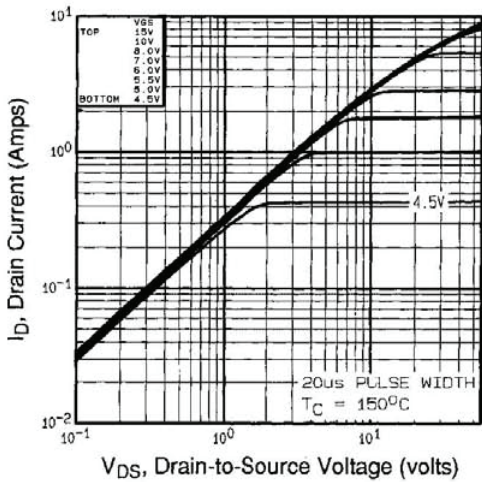


Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^\circ\text{C}$

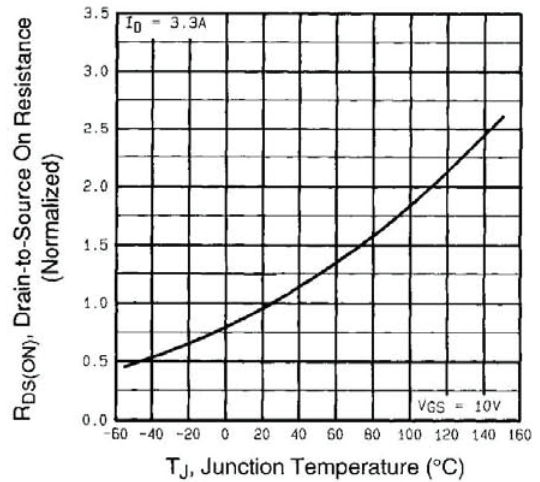


Fig. 4 - Normalized On-Resistance vs. Temperature

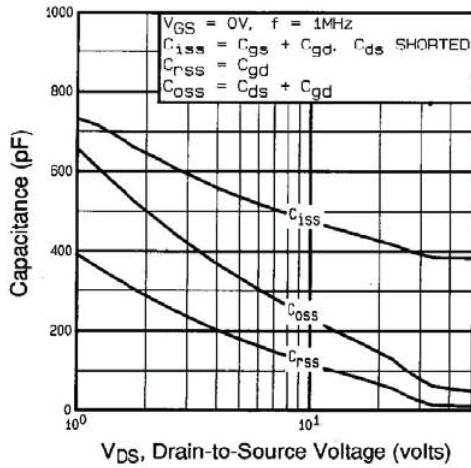


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

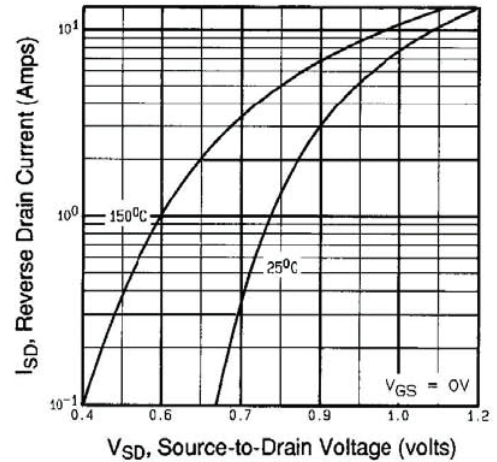


Fig. 7 - Typical Source-Drain Diode Forward Voltage

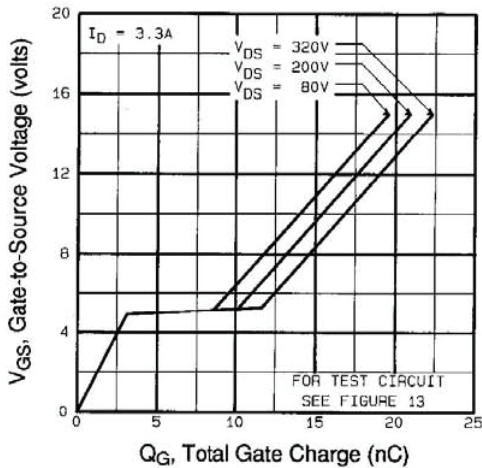


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

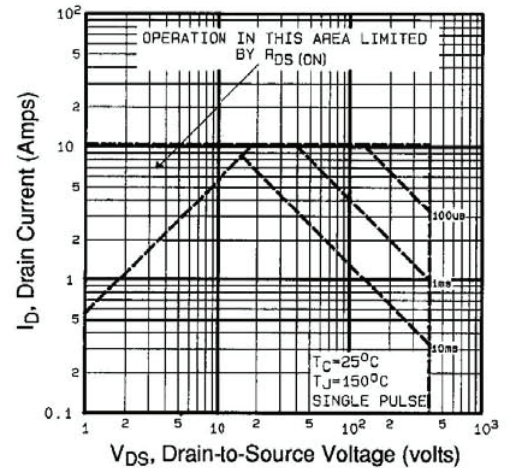


Fig. 8 - Maximum Safe Operating Area

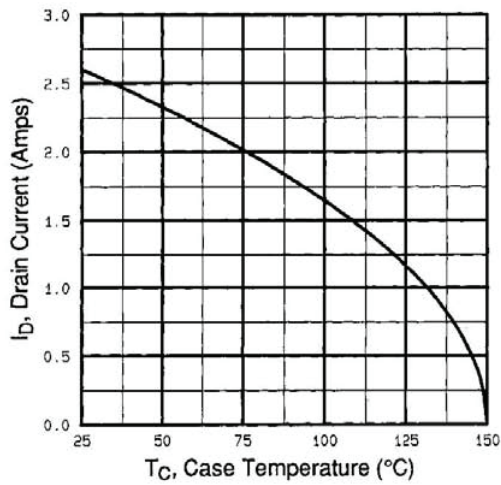


Fig. 9 - Maximum Drain Current vs. Case Temperature

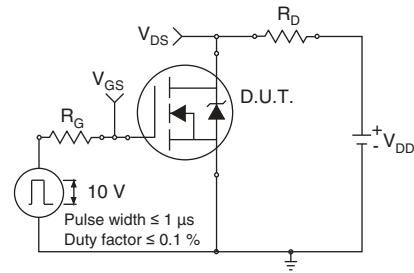


Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms

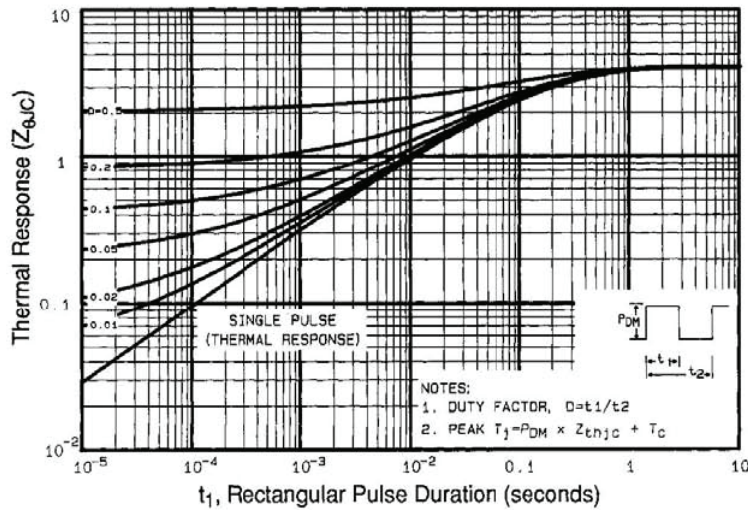


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

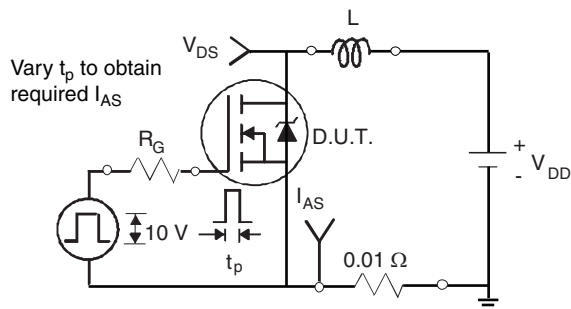


Fig. 12a - Unclamped Inductive Test Circuit

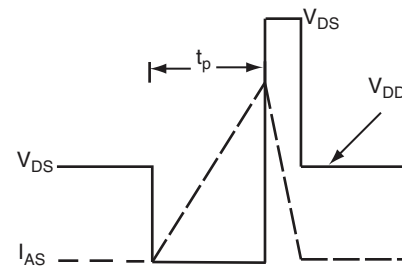


Fig. 12b - Unclamped Inductive Waveforms

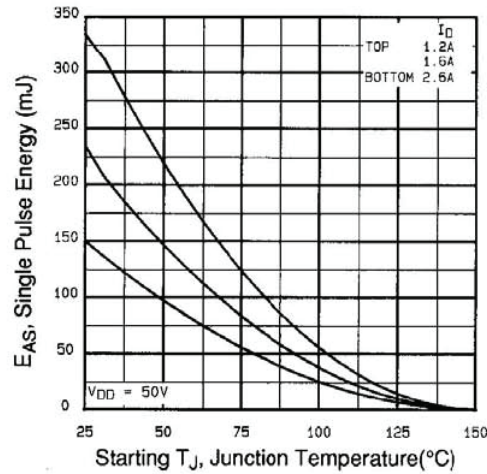


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

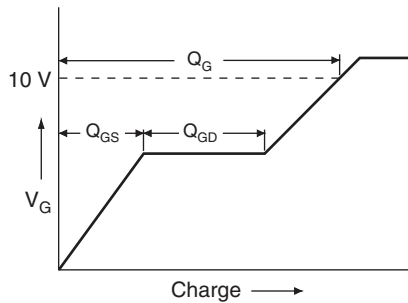


Fig. 13a - Basic Gate Charge Waveform

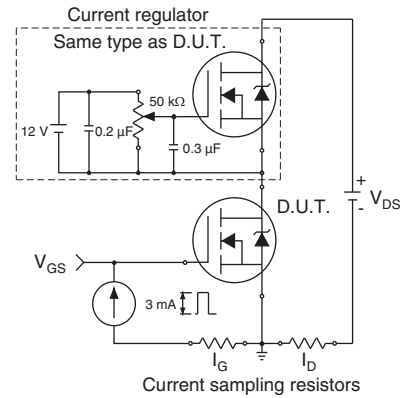


Fig. 13b - Gate Charge Test Circuit

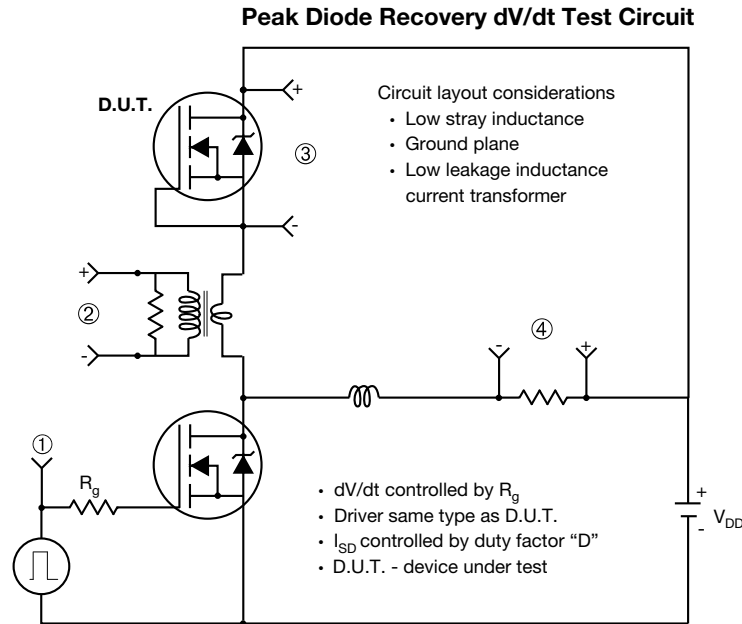


Fig. 14 - For N-Channel

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